



# Bipolar NPN Bare Die – BTN6028

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## Part Description

The BTN6028 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 300V
- VCEO = 200V
- VEBO = 7V
- hFE = 190-450 @ VCE = 5V, IC = 0.1A
- VCE(Sat) = 0.18V @ IC = 1A, IB = 50mA
- fT = 90 MHz @ VCE = 10V, IE = 0A
- COBO = 16pF @ VCB = 10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SD1857

## Die Size (Unawn)

1300 $\mu$ m X 1300 $\mu$ m, 51 Mils X 51 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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